

Amendments to the Claims (NONE)

Claims 1-7 (canceled).

Claim 8 (previously presented) The method of claim 16 wherein the etching comprises plasma etching.

Claim 9 (previously presented) The method of claim 16 wherein the etching comprises magnetically enhanced plasma etching.

Claim 10 (previously presented) The method of claim 16 wherein the etching comprises substantially anisotropic etching of the silicon nitride comprising layer.

Claims 11-13 (canceled).

Claim 14 (previously presented) The method of claim 16 wherein the etching chemistry comprises at least two fluorocarbons.

Claim 15 (previously presented) The method of claim 16 wherein the etching chemistry comprises at least three fluorocarbons.

Claim 16 (previously presented) A method of forming integrated circuitry comprising:

forming a layer comprising silicon nitride over a semiconductor substrate;

forming a patterned photoresist comprising masking layer over the silicon nitride layer, the patterned masking layer comprising mask openings therethrough; and

etching the silicon nitride comprising layer through the mask openings substantially selectively to the photoresist comprising layer using an etching chemistry having reactive components consisting of ammonia and at least one fluorocarbon under etching conditions effective to substantially anisotropically etch the silicon nitride comprising layer, the etching chemistry comprising a volumetric ratio of all fluorocarbon to the ammonia of from 40:1 to 20:1 and providing increased selectivity to the photoresist comprising masking layer than would otherwise occur using identical etching chemistry and identical etching conditions without any ammonia.

Claims 17 and 18 (canceled).

Claim 19 (original) The method of claim 16 wherein the fluorocarbon comprises a hydrofluorocarbon.

Claim 20 (previously presented) A method of forming integrated circuitry comprising:

forming a layer comprising silicon nitride over a semiconductor substrate;
forming a patterned photoresist comprising masking layer over the silicon nitride layer, the patterned masking layer comprising mask openings therethrough; and

etching the silicon nitride comprising layer through the mask openings substantially selectively to the photoresist comprising layer using an etching chemistry having reactive components consisting of ammonia and at least one fluorocarbon under etching conditions effective to substantially anisotropically etch the silicon nitride comprising layer, the etching chemistry comprising a volumetric ratio of all fluorocarbon to the ammonia of from 40:1 to 20:1 and providing increased selectivity to the photoresist comprising masking layer than would otherwise occur using identical etching chemistry and identical etching conditions without any ammonia, wherein the fluorocarbon is at least one member selected from the group consisting of C_4F_6 and C_5F_8 .

Claim 21 (original) The method of claim 16 wherein the silicon nitride comprising layer consists essentially of silicon nitride.

Claims 22-46 (canceled).

Claim 47 (previously presented) The method of claim 16 wherein the photoresist comprises 193 nanometer photoresist.

Claim 48 (previously presented) The method of claim 16 comprising introducing the ammonia and fluorocarbon successively into a reaction chamber in which the substrate is received during the etching.

Claim 49 (previously presented) The method of claim 16 wherein the integrated circuitry forming comprises forming shallow trench isolation within the semiconductor substrate, the photoresist comprising masking layer being patterned effective to form a plurality of shallow trench mask openings therethrough.

Claim 50 (previously presented) The method of claim 16 wherein the integrated circuitry forming comprises forming shallow trench isolation within the semiconductor substrate, the silicon nitride comprising layer being formed over a bulk semiconductor substrate, and the photoresist comprising masking layer being patterned effective to form a plurality of shallow trench mask openings therethrough.

Claim 51 (previously presented) The method of claim 20 wherein the fluorocarbon comprises C_4F_6 .

Claim 52 (previously presented) The method of claim 20 wherein the fluorocarbon comprises C_5F_8 .

Claim 53 (canceled).

Claim 54 (previously presented) The method of claim 20 wherein the photoresist comprises 193 nanometer photoresist.

Claim 55 (previously presented) The method of claim 20 comprising introducing the ammonia and fluorocarbon successively into a reaction chamber in which the substrate is received during the etching.

Claim 56 (canceled).

Claim 57 (previously presented) The method of claim 20 wherein the etching comprises plasma etching.

Claim 58 (previously presented) The method of claim 20 wherein the etching comprises magnetically enhanced plasma etching.

Claim 59 (previously presented) The method of claim 20 wherein the etching comprises substantially anisotropic etching of the silicon nitride comprising layer.

Claim 60 (previously presented) The method of claim 20 wherein the etching chemistry comprises at least two fluorocarbons.

Claim 61 (previously presented) The method of claim 20 wherein the etching chemistry comprises at least three fluorocarbons.

Claim 62 (canceled).

Claim 63 (previously presented) The method of claim 20 wherein the integrated circuitry forming comprises forming shallow trench isolation within the semiconductor substrate, the photoresist comprising masking layer being patterned effective to form a plurality of shallow trench mask openings therethrough.

Claim 64 (previously presented) The method of claim 20 wherein the integrated circuitry forming comprises forming shallow trench isolation within the semiconductor substrate, the silicon nitride comprising layer being formed over a bulk semiconductor substrate, and the photoresist comprising masking layer being patterned effective to form a plurality of shallow trench mask openings therethrough.